

Abstract

The present invention provides a high efficient nitride semiconductor element having an opposed terminal structure, whose terminals facing each other, and a method for producing thereof.

5 The nitride semiconductor element includes a conductive layer, a first terminal, a nitride semiconductor with a light-emitting layer, and a second terminal, on a supporting substrate successively. The first terminal and a first insulating protect layer are interposed between the conductive layer and a first conductive type nitride semiconductor layer.

10 The method includes: a growing step for growing the nitride semiconductor further having an undoped GaN layer on a different material substrate; subsequently, a attaching step for attaching the supporting substrate to the first conductive type nitride semiconductor layer side of the nitride semiconductor with interposing the first terminal between them; and subsequently,

15 an exposing step for exposing the second conductive type nitride semiconductor layer by eliminating the different material substrate and the undoped GaN.